

MOSFET Silicon N-Channel MOS

1. Applications

Single-ended flyback or two-transistor forward topologies.
PC power, PD Adaptor, LCD & PDP TV and LED lighting.



2. Features

Low drain-source on-resistance: $R_{DS(ON)} = 5.5\text{m}\Omega$ (typ.)
Easy to control Gate switching
Enhancement mode: $V_{th} = 2.4$ to 3.4 V

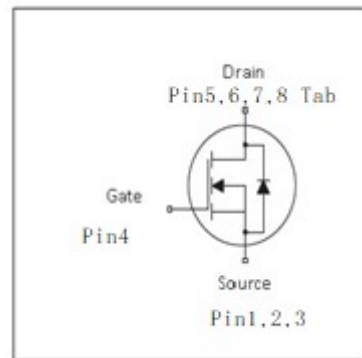
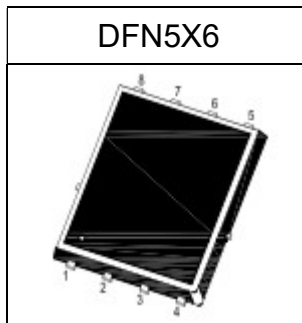


Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	100	V
$R_{DS(on),max}$	6.3	$\text{m}\Omega$
$Q_{g,typ}$	60.7	nC
$I_{D,pulse}$	396	A

3. Packaging and Internal Circuit

Part Name	Package	Marking
AUN063N10	DFN5X6	AUN063N10



1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D		-	123	A	$T_C=25^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	396	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	240	mJ	$T_C=25^\circ\text{C}$, $V_{DD}=50\text{V}$, $I=31\text{A}$, $L=0.5\text{mH}$, $R_G=25\Omega$
Avalanche current, single pulse	I_{AR}	-	-	31	A	$T_C=25^\circ\text{C}$, $V_{DD}=50\text{V}$, $L=0.5\text{mH}$, $R_G=25\Omega$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Power dissipation	P_{tot}	-	-	151	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	
Transconductance	GFS	-	51	-	S	$V_{DS}=5\text{V}$ $I_{DS}=20\text{A}$

¹⁾ Limited by $T_{j,max}$. Maximum Duty Cycle $D = 0.50$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_G

2 Thermal characteristics

Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	1.3	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	50	°C/W	device on PCB, minimal footprint

3 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{(GS)th}$	2.4		3.4	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=95V, V_{GS}=0V, T_j=25^\circ C$
Gate-source leakage current	I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	5.5	6.3	m Ω	$V_{GS}=10V, I_D=20A, T_j=25^\circ C$
Gate resistance (Intrinsic)	R_G	-	1	-	Ω	$f=1\text{MHz}$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	3680	-	pF	$V_{GS}=0V, V_{DS}=50V, f=1\text{MHz}$
Output capacitance	C_{oss}	-	361	-	pF	$V_{GS}=0V, V_{DS}=50V, f=1\text{MHz}$
Reverse transfer capacitance	C_{rss}	-	14.6	-	pF	$V_{GS}=0V, V_{DS}=50V, f=1\text{MHz}$
Turn-on delay time	$t_{d(on)}$	-	29	-	ns	$V_{DD}=50V, V_{GS}=10V, I_D=20A, R_G=10\Omega$
Rise time	t_r	-	55	-	ns	$V_{DD}=50V, V_{GS}=10V, I_D=20A, R_G=10\Omega$
Turn-off delay time	$t_{d(off)}$	-	69	-	ns	$V_{DD}=50V, V_{GS}=10V, I_D=20A, R_G=10\Omega$
Fall time	t_f	-	43	-	ns	$V_{DD}=50V, V_{GS}=10V, I_D=20A, R_G=10\Omega$

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	15.5	-	nC	$V_{DD}=50V, I_D=20A, V_{GS}=0 \text{ to } 10V$
Gate to drain charge	Q_{gd}	-	17.6	-	nC	$V_{DD}=50V, I_D=20A, V_{GS}=0 \text{ to } 10V$
Gate charge total	Q_g	-	60.7	-	nC	$V_{DD}=50V, I_D=20A, V_{GS}=0 \text{ to } 10V$

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.7	-	V	$V_{GS}=0V, I_F=1A, T_j=25^\circ C$
Reverse recovery time	t_{rr}	-	45	-	ns	$V_R=30V, I_F=20A, di_F/dt=300A/\mu s$
Reverse recovery charge	Q_{rr}	-	212	-	nC	$V_R=30V, I_F=20A, di_F/dt=300A/\mu s$
Peak reverse recovery current	I_{rrm}	-	8.4	-	A	$V_R=30V, I_F=20A, di_F/dt=300A/\mu s$

4 Test Circuits

Table 8 Diode characteristics

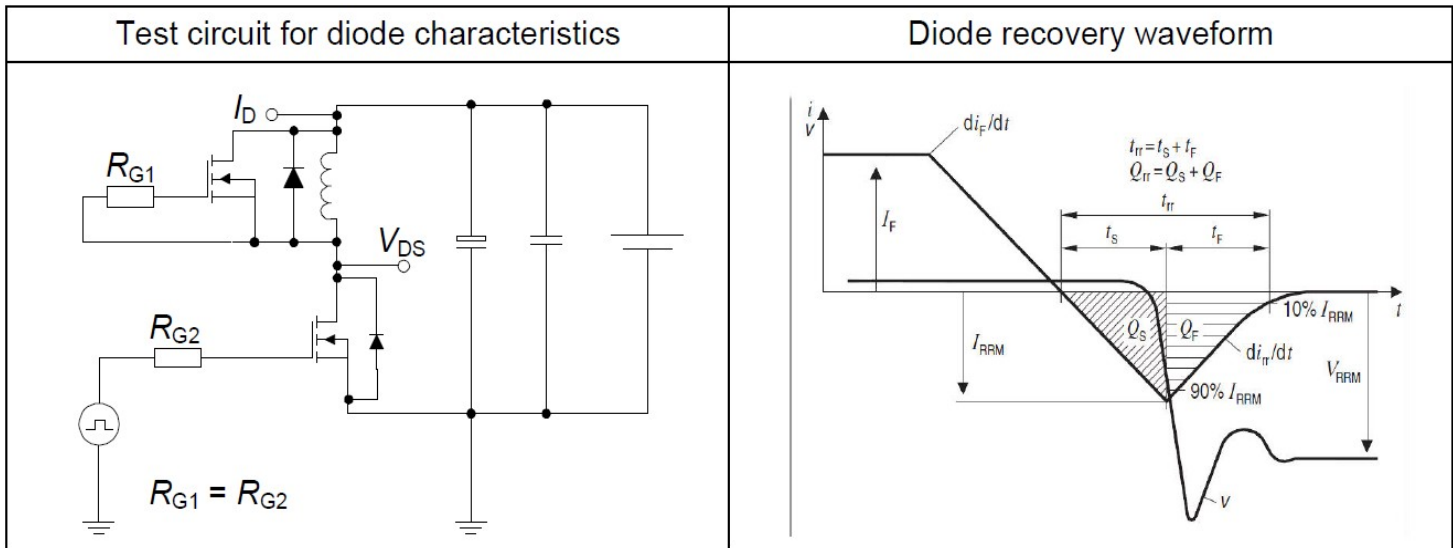


Table 9 Switching times

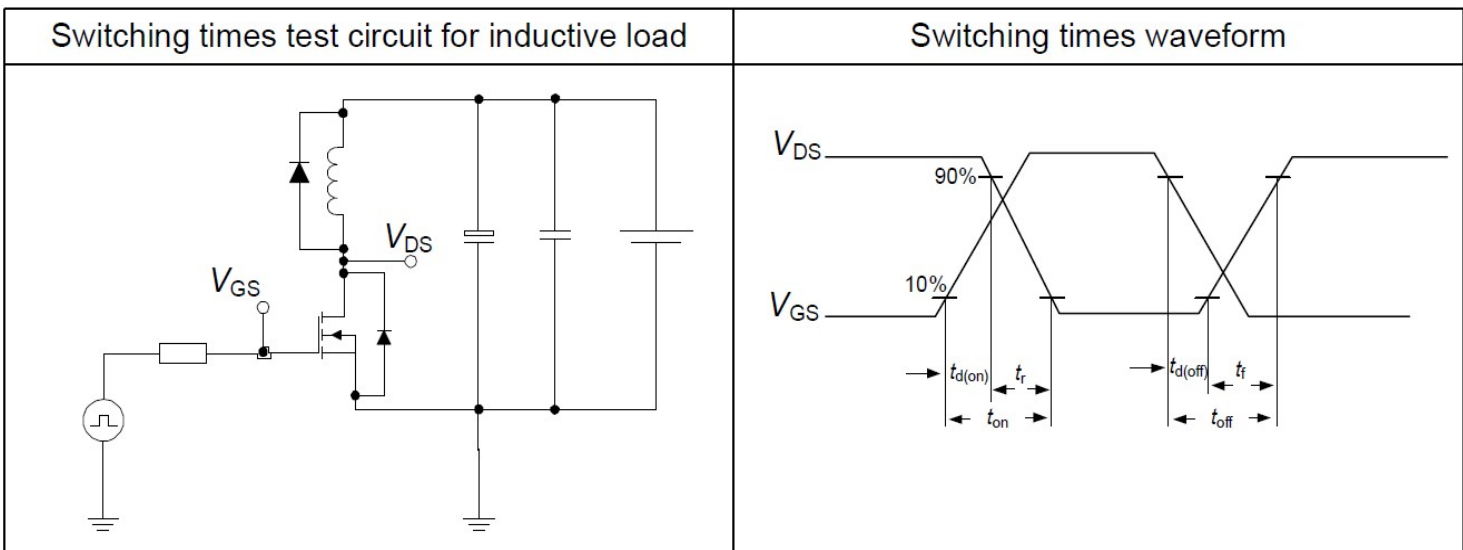
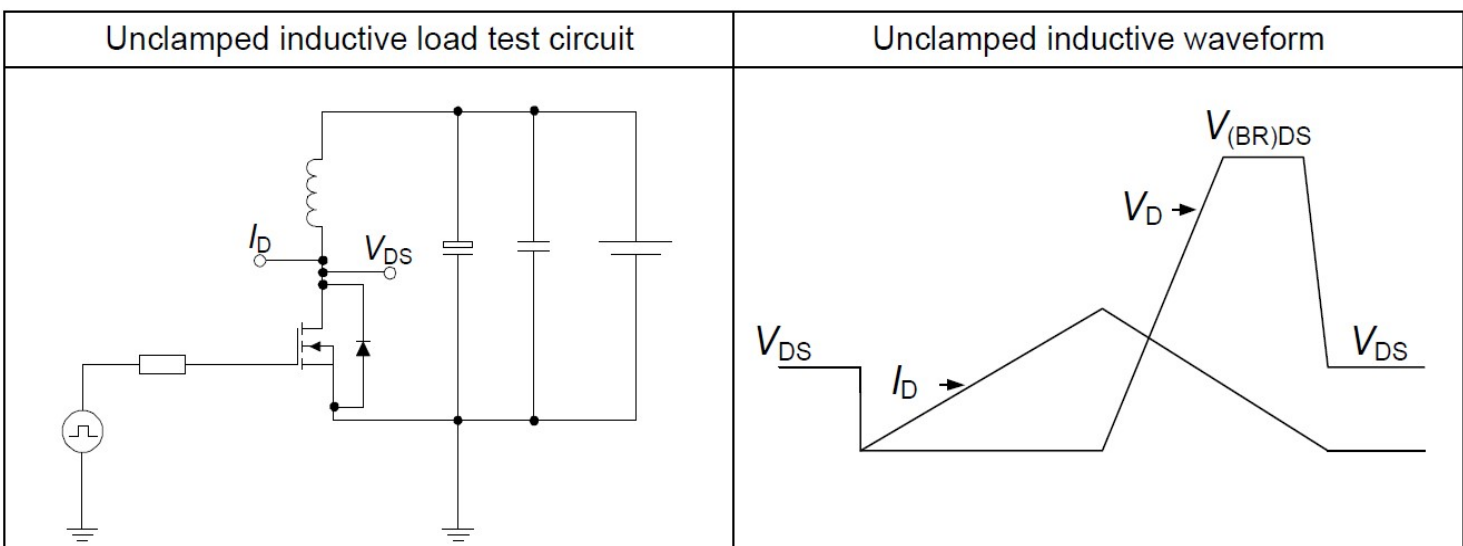
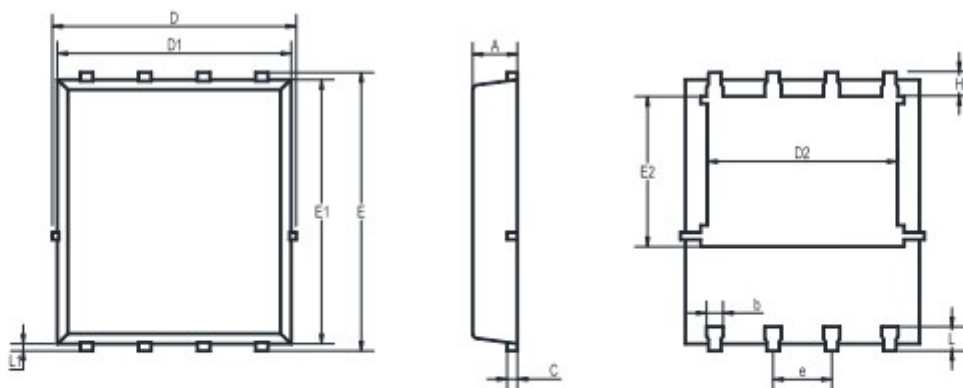


Table 10 Unclamped inductive load



5 Package Outlines



UNIT	A	b	C	D	D1	D2	E	E1	E2	e	L	L1	H
mm	1.12	0.51	0.34	5.26	5.1	4.5	6.25	6	3.66	1.37	0.71	0.2	0.71
	0.9	0.33	0.11	4.7	4.7	3.56	5.75	5.6	3.18	1.17	0.35	0.06	0.35

Outline PG-DFN5X6

Revision History

Revision	Date	Subjects (major changes since last revision)
1.0	2021-12-02	Preliminary version

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